CMSA6504A

N-Channel Enhancement Mode Field Effect Transistor

General Description

The CMSA6504A uses advanced trench technology to provide excellent RDS (ON), low gate charge and minimize the loss of power conversion applications. This device is suitable to be used as the low side FET in SMPS, load switching and general purpose.

Product Summary

BVDSS	RDSON	ID
30V	1.8mΩ	85A

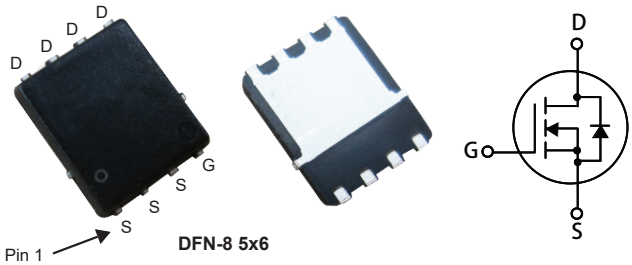
Applications

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

Features

- RDS(ON)<1.8mΩ @ VGS=10V
- 100% avalanche tested
- Conduction losses reduced
- Switching losses reduced

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA6504A	DFN-8 5*6	CMSA6504A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current	85	A
EAS	Single Pulse Avalanche Energy	800	mJ
I_{DM}	Pulsed Drain Current	255	A
P_D@T_C=25℃	Total Power Dissipation	50	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	---	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	2.5	℃/W

Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=28A	---	---	1.8	mΩ
		V_{GS}=4.5V , I_D=25A	---	---	2.8	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250μA	1.0	---	3.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V ,V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V, V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V, I_D=25A	---	40	---	S
Q_g	Total Gate Charge	V_{DS}=15V , I_D=20A V_{GS}=10V	---	44	---	nC
Q_{gs}	Gate-Source Charge		---	9	---	
Q_{gd}	Gate-Drain Charge		---	7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=15V , V_{GS}=10V , R_L=0.75Ω R_{GEN} =3Ω	---	12	---	ns
T_r	Rise Time		---	6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	41	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	6300	---	pF
C_{oss}	Output Capacitance		---	600	---	
C_{rss}	Reverse Transfer Capacitance		---	580	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	V_G=V_D=0V , Force Current	---	---	85	A
I_{SM}	Pulsed Source Current		---	---	255	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=28A , Tj=25℃	---	---	1.2	V

Note:

This product has been designed and qualified for the counsumer market.
Cmos assumes no liability for customers' product design or applications.
Cmos reserver the right to improve product design ,functions and reliability wihtout notice.